International
IOR Rectifier

PD - 96226

IRF8734PbF

HEXFET® Power MOSFET

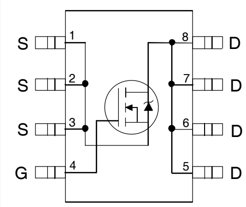
V_{DSS}	$R_{DS(on)}$ max	Qg (typ.)
30V	3.5mΩ@V_{GS} = 10V	20nC

Applications

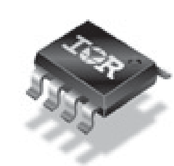
- Synchronous MOSFET for Notebook Processor Power
- Synchronous Rectifier MOSFET for Isolated DC-DC Converters in Networking Systems

Benefits

- Very Low $R_{DS(on)}$ at 4.5V V_{GS}
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current
- 100% Tested for R_G
- Lead-Free



Top View


SO-8

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	21	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	17	
I_{DM}	Pulsed Drain Current ①	168	
P_D @T_A = 25°C	Power Dissipation ④	2.5	W
P_D @T_A = 70°C	Power Dissipation ④	1.6	
	Linear Derating Factor	0.02	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	——	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④	——	50	

Notes ① through ⑤ are on page 10

ORDERING INFORMATION:
See detailed ordering and shipping information on the last page of this data sheet.

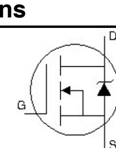
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V_{GS} = 0V, I_D = 250μA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.023	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	2.9	3.5	mΩ	V_{GS} = 10V, I_D = 21A ③
		—	4.2	5.1		V_{GS} = 4.5V, I_D = 17A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.80	2.35	V	V_{DS} = V_{GS}, I_D = 50μA
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-6.5	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V_{DS} = 24V, V_{GS} = 0V
		—	—	150		V_{DS} = 24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
gfs	Forward Transconductance	85	—	—	S	V_{DS} = 15V, I_D = 17A
Q_g	Total Gate Charge	—	20	30	nC	
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	5.2	—		V_{DS} = 15V
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	2.3	—		V_{GS} = 4.5V
Q_{gd}	Gate-to-Drain Charge	—	6.9	—		I_D = 17A
Q_{godr}	Gate Charge Overdrive	—	5.4	—		See Figs. 16a &16b
Q_{sw}	Switch Charge (Q_{gs2} + Q_{gd})	—	9.2	—		
Q_{oss}	Output Charge	—	15	—	nC	V_{DS} = 16V, V_{GS} = 0V
R_G	Gate Resistance	—	1.7	3.1	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	13	—	ns	V_{DD} = 15V, V_{GS} = 4.5V ③
t_r	Rise Time	—	16	—		I_D = 17A
$t_{d(off)}$	Turn-Off Delay Time	—	15	—		R_G = 1.8Ω
t_f	Fall Time	—	8.0	—		See Figs. 15a &15b
C_{iss}	Input Capacitance	—	3175	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	627	—		V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	—	241	—		f = 1.0MHz

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	216	mJ
I_{AR}	Avalanche Current ①	—	17	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	168		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	T_J = 25°C, I_S = 17A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	20	30	ns	T_J = 25°C, I_F = 17A, V_{DD} = 15V
Q_{rr}	Reverse Recovery Charge	—	25	38	nC	di/dt = 345A/μs ③

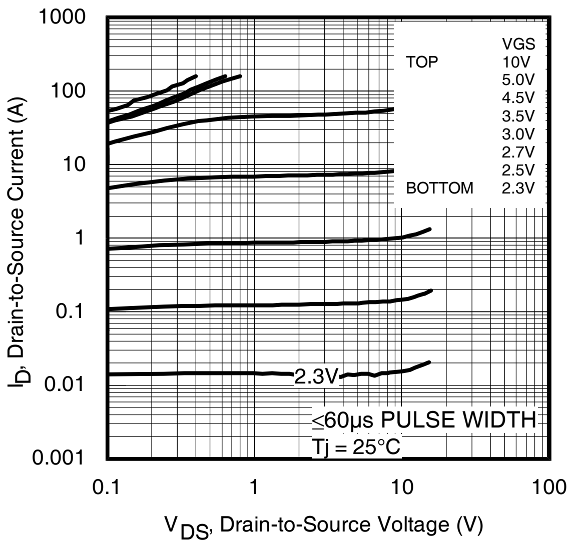


Fig 1. Typical Output Characteristics

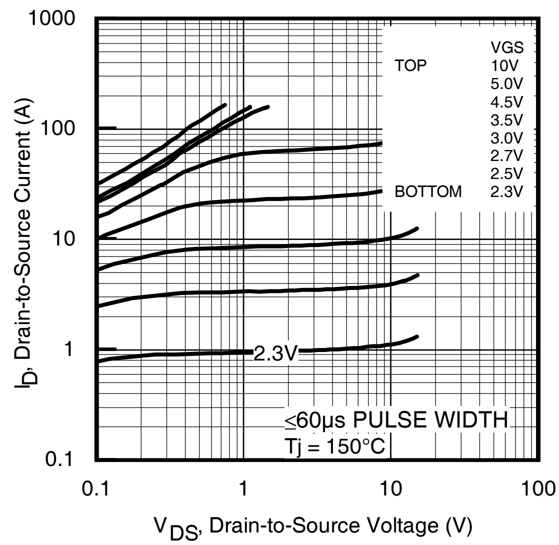


Fig 2. Typical Output Characteristics

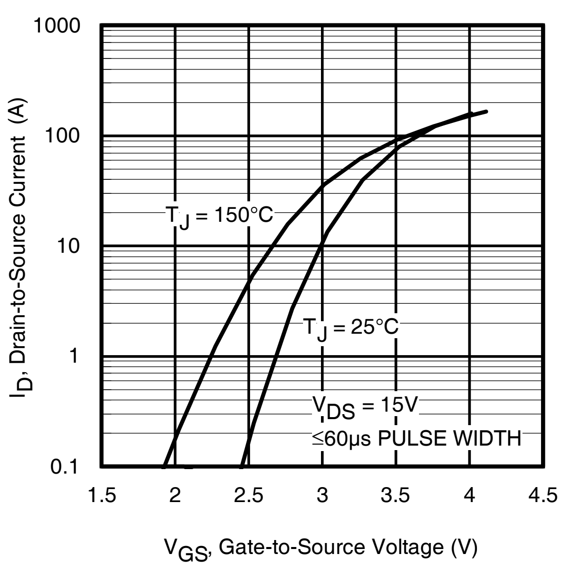


Fig 3. Typical Transfer Characteristics

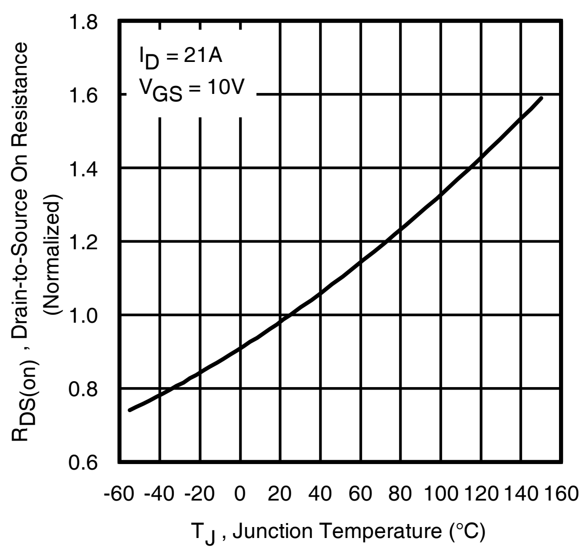


Fig 4. Normalized On-Resistance Vs. Temperature

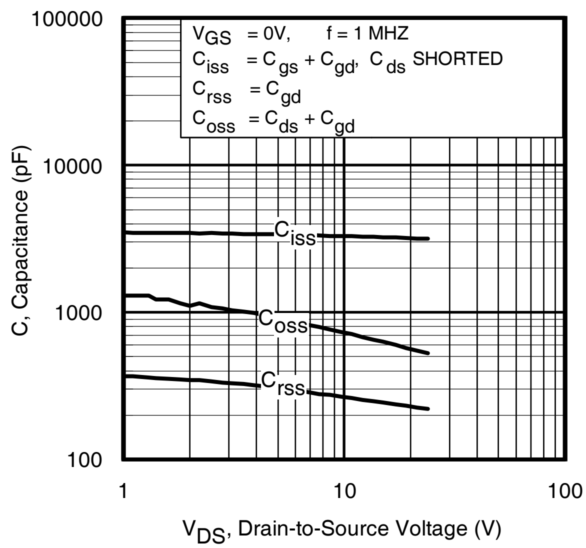


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

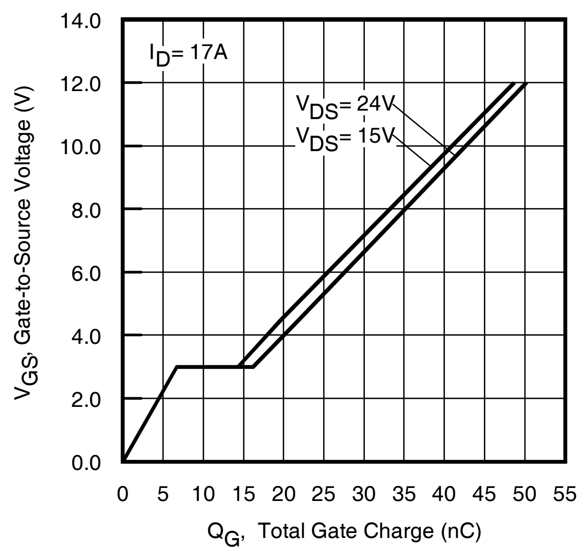


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

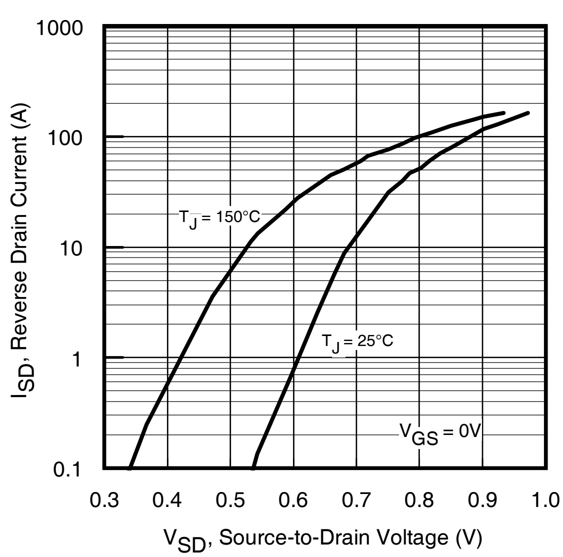


Fig 7. Typical Source-Drain Diode Forward Voltage

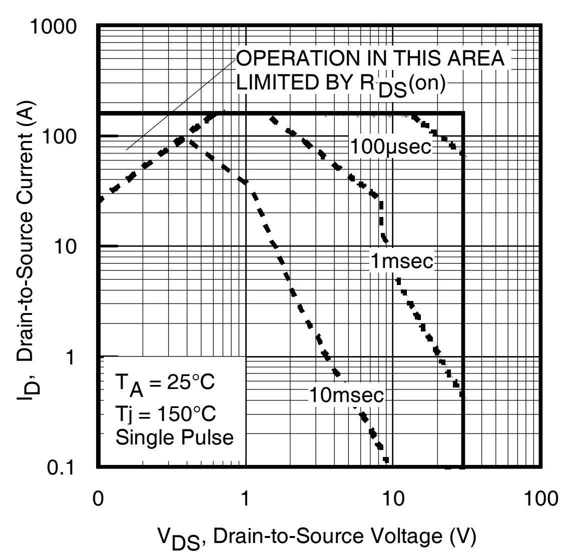


Fig 8. Maximum Safe Operating Area

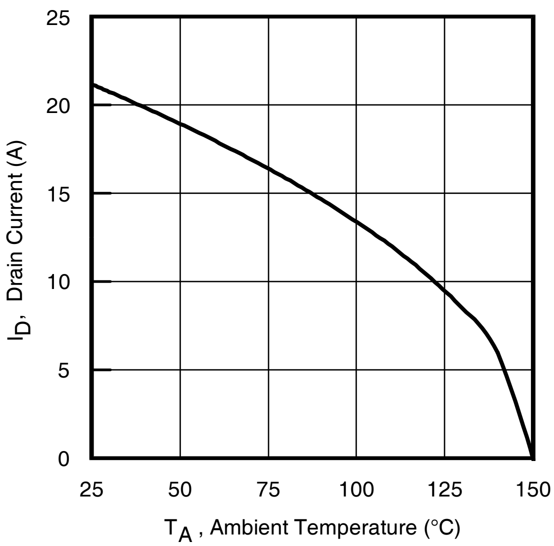


Fig 9. Maximum Drain Current Vs. Ambient Temperature

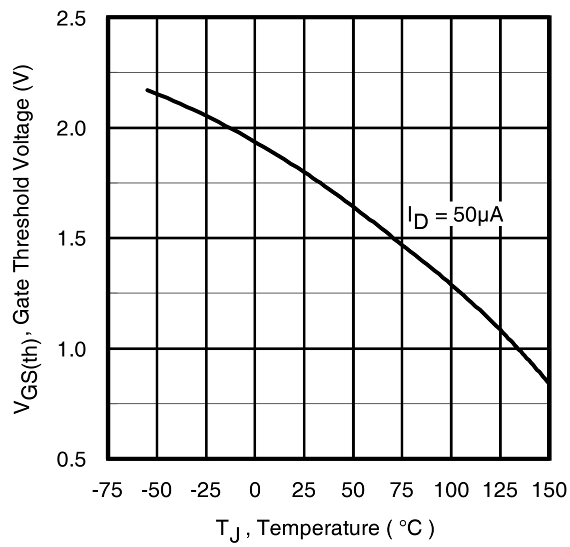


Fig 10. Threshold Voltage Vs. Temperature

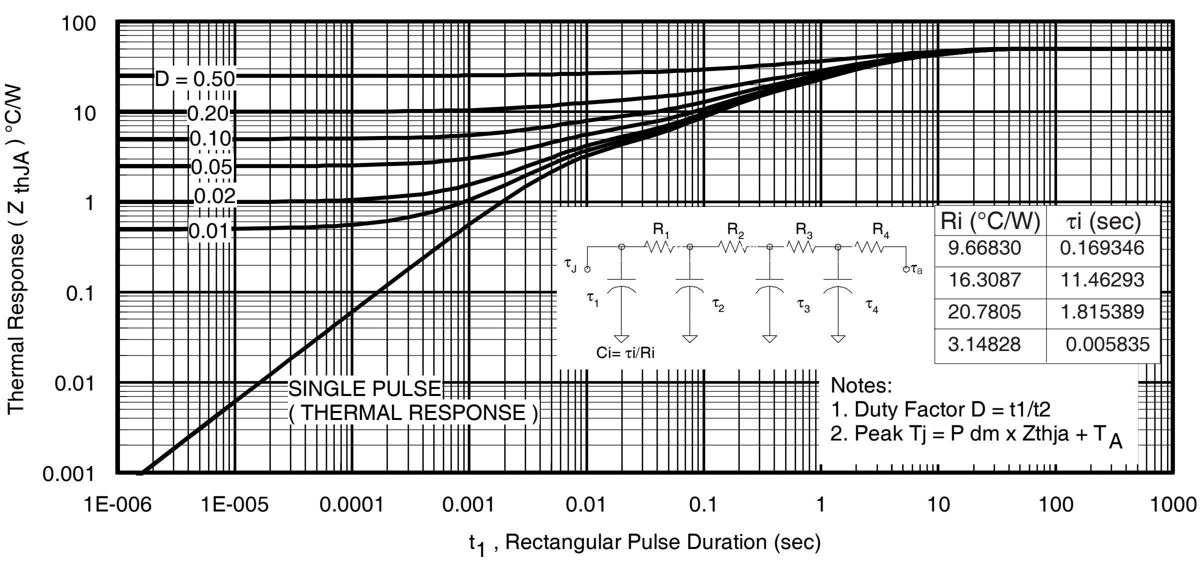


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

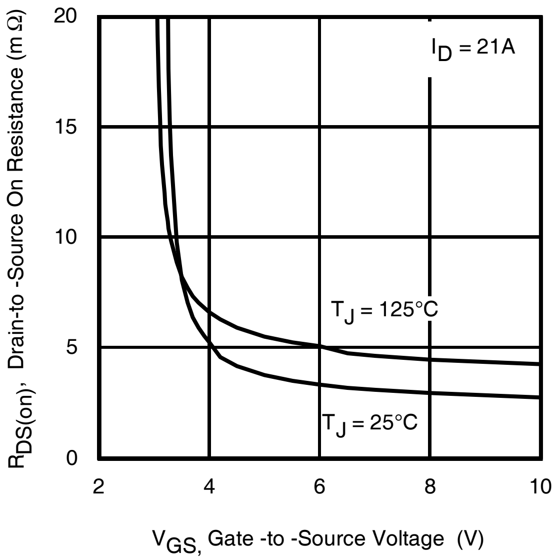


Fig 12. On-Resistance Vs. Gate Voltage

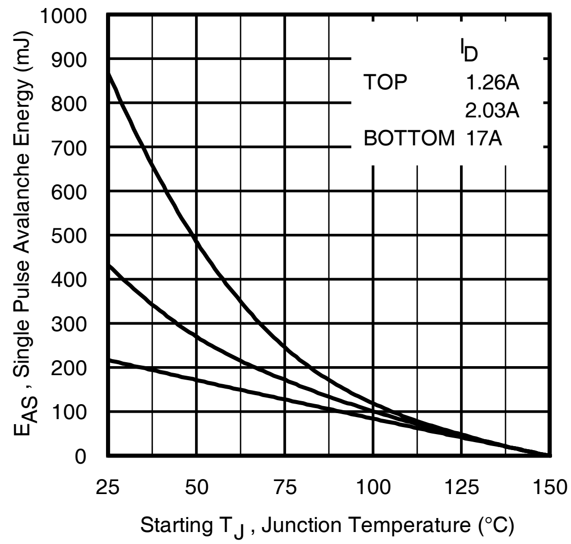


Fig 13c. Maximum Avalanche Energy Vs. Drain Current

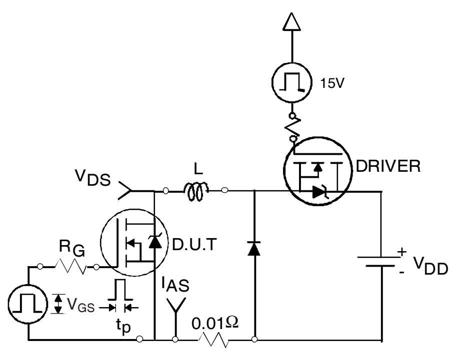


Fig 14a. Unclamped Inductive Test Circuit

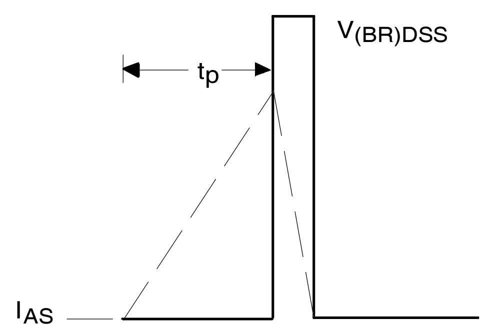


Fig 14b. Unclamped Inductive Waveforms

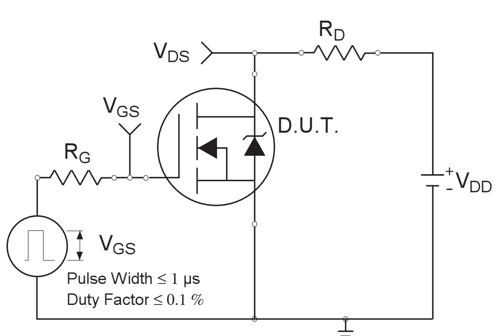


Fig 15a. Switching Time Test Circuit

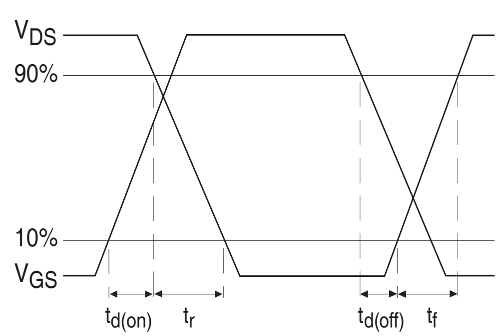


Fig 15b. Switching Time Waveforms

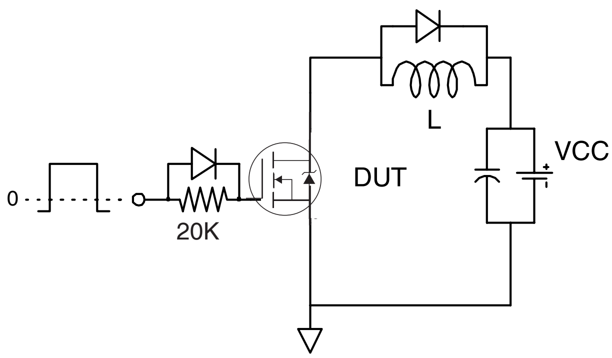


Fig 16a. Gate Charge Test Circuit

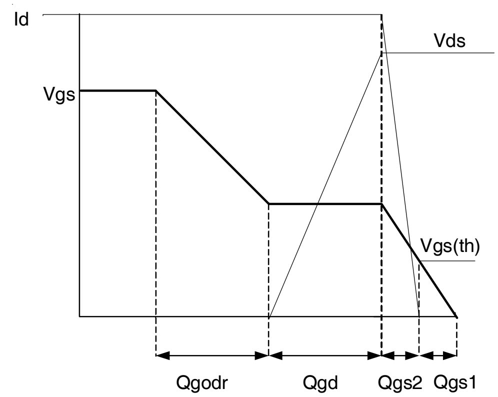
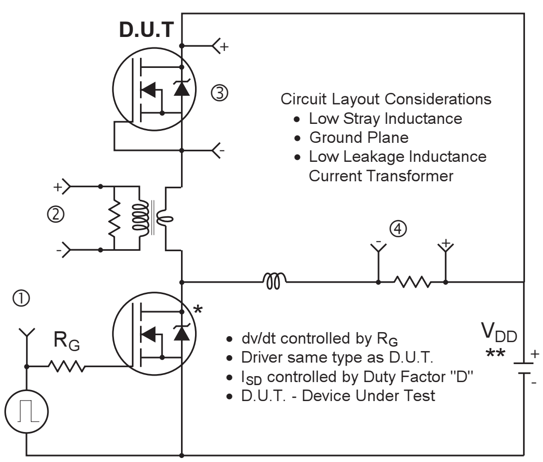
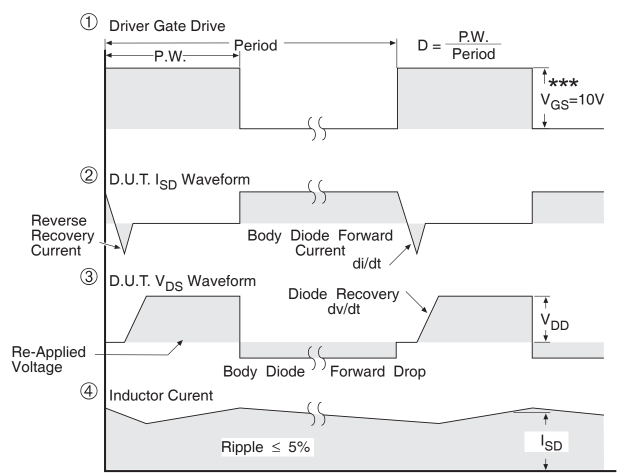


Fig 16b. Gate Charge Waveform



* Use P-Channel Driver for P-Channel Measurements
** Reverse Polarity for P-Channel

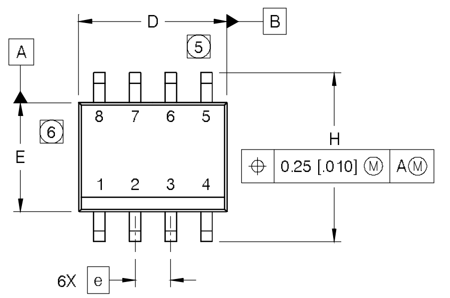


*** V_{GS} = 5V for Logic Level Devices

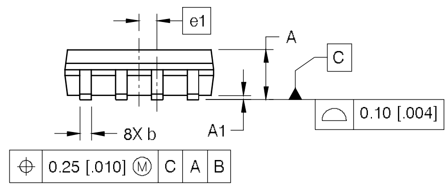
Fig 17. Diode Reverse Recovery Test Circuit for HEXFET® Power MOSFETs

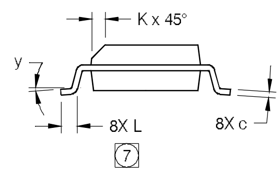
SO-8 Package Outline(Mosfet & Fetky)

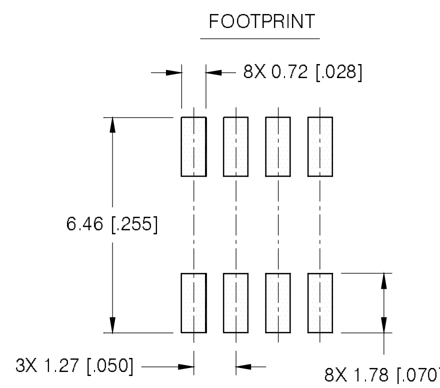
Dimensions are shown in milimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°







NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.

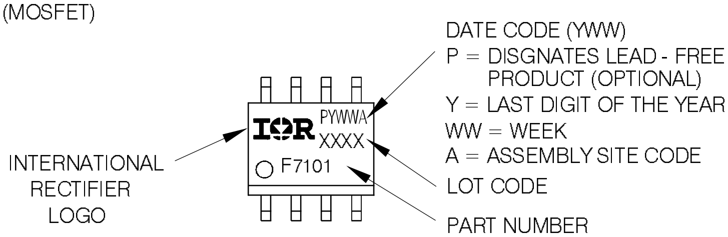
5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].

6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].

7 DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

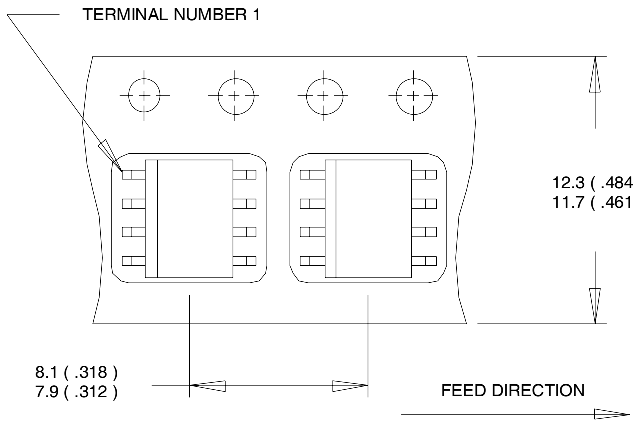
SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

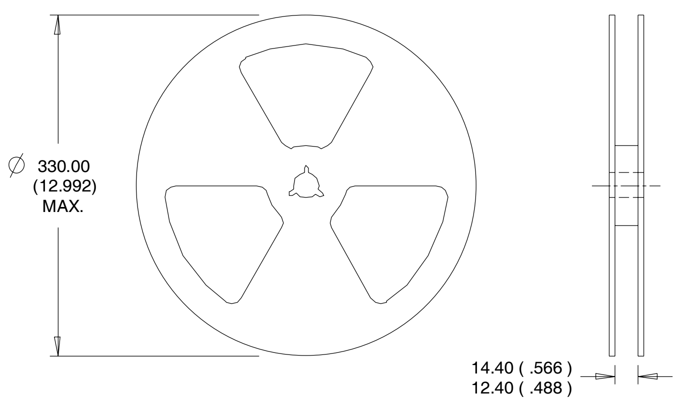


Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

SO-8 Tape and Reel (Dimensions are shown in milimeters (inches))



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRF8734PbF	SO-8	Tube/Bulk	95	
IRF8734TRPbF	SO-8	Tape and Reel	4000	

Qualification Information†

Qualification level	Consumer ††	
	(per JEDEC JESD47F††† guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D†††)
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site http://www.irf.com/product-info/reliability

†† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information: http://www.irf.com/whoto-call/salesrep/

††† Applicable version of JEDEC standard at the time of product release.

Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 1.69mH R_G = 25Ω, I_{AS} = 16A.

③ Pulse width ≤ 400μs; duty cycle ≤ 2%.

④ When mounted on 1 inch square copper board

⑤ R_θ is measured at T_J of approximately 90°C.

Data and specifications subject to change without notice

International
IOR Rectifier

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